

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	"93128579"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 10:15
L2	15	"366565"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 10:17
L3	8	"544895"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 10:19
L4	33	"6291334"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 10:19
L5	2	"6291334".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 10:19
L6	3833362	copper metal metallization	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 11:59
L7	293577	etchstop etch adj stop sic sin silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 12:36
L8	679223	nm nanometer nano adj meter angstrom ang ".ang."	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 10:23
L9	1088220	(micron "mu.m" mu)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 10:23
L10	137308	("200" "300") adj2 L8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 11:04

L11	117383	("2" "0.2" ".3" "0.3") adj2 L9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 11:08
L12	233997	L10 L11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 10:23
L13	4197	L12 near4 L7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 10:23
L14	8304703	layer film line trace	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 10:23
L15	478294	L6 near2 L14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 10:23
L16	256	L13 same L15	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 10:23
L17	1155822	damage defective	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 10:23
L18	2719	L17 near5 L15	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 10:23
L19	15	L16 and L18	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 10:33
L20	213166	("100" "200" "300") adj2 L8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 11:04

L21	52252	("01" "02" "03" "0.01" "0.02" "0.03" ) adj2 L9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 11:58
L22	254970	20 21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 11:58
L23	7236	7 near5 22	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 12:37
L24	592595	(copper metal metallization conduct\$4) near 14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 12:04
L25	7001955	layer film level	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 12:11
L26	611186	(insulat\$4 dielectric) near 25 ILD IMD	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 12:29
L27	13779	7 with 24	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 12:37
L28	52112	7 with 26	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 12:38
L29	143	23 same 27 same 28	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 12:31
L30	4187635	thinner less smaller	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 12:31

L31	36363	30 near3 22	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 12:32
L32	8	29 and 31	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 12:32
L33	35110	etchstop etch adj stop stop near2 (layer film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 12:37
L34	600	33 near5 22	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 12:37
L35	4346	33 with 24	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 12:37
L36	9182	33 with 26	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 12:38
L37	15	34 same 35 same 36	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 12:38
L38	4	("6146987").URPN.	USPAT	OR	ON	2006/01/07 12:58